# Innogration (Suzhou) Co., Ltd.

## DC-3GHz, 15W, 50V GaN Fully matched PA Module

#### Description

The SMAV0030-15 is a 15-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from 30MHz to 3GHz. The module is 50  $\Omega$  input/output matched and requires minimal external components.

The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.



#### Vds=50V, Idq=25mA, CW

Parameter	30MHz	0.5GHz	1.0GHz	1.5GHz	2.0GHz	2.5GHz	3.0GHz	Units
Small signal Gain	17.5	17.2	16.5	15.6	15.0	14.5	13	dB
Psat	21.3	20.2	20.6	18.6	15.9	15.9	20.1	W
Gain@Psat	14.5	14.2	13.5	12.6	12.0	11.5	10	dB
Eff@Psat	71	57	57	49	40	43	46	%

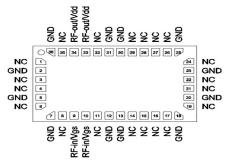
#### **Product Features**

- Operating Frequency Range: 30MHz-3GHz
- Operating Drain Voltage: +50 V
- 50 Ω Input/Output
- P3dB: ≥15W
- Small signal gain:>13dB, Power gain:>10dB
- Minimum efficiency:40%
- 6x10 mm Surface Mount Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

#### Applications

- Ultra Broadband Amplifiers
- L band pulsed power Amplifier
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

#### **Pin Configuration and Description**



Top View

## in Innogration (Suzhou) Co., Ltd.

Document Number: SMAV0030-15 Production Datasheet V1.0

Pin No.	Symbol			Description		
33,34	RFout/Vdd	Transis	Transistor 1, Drain Bias & RF Output			
9,10	RFin/Vgs	Transis	Transistor 1, RF Input &Gate Bias			
Others NC		No con	No connection			
2,5,7,12, 13,18,20,23,25, 30, 31,36 Package Base	GND	vias for	DC/RF Ground. Must be soldered to EVB ground plane over array o vias for thermal and RF performance. Solder voids under Pkg Base wil result in excessive junction temperatures causing permanent damage.			
Table 1. Maximum Ratings	1					
Rating		Symbol		Value		Unit
DrainSource Voltage		$V_{\text{DSS}}$		200		Vdc
GateSource Voltage		$V_{\text{GS}}$		-10 to +2		Vdc
Operating Voltage		$V_{\text{DD}}$		+55		Vdc
Storage Temperature Range		Tstg		-65 to +150		°C
Case Operating Temperature		Tc		+150		°C
Operating Junction Temperature		TJ		+225		°C
Table 2. Thermal Characteristics			·			
Characteristic		Symbol		Value		Unit
Thermal Resistance, Junction to Case $T_c$ = 25°C, DC test	Rejc		6.5			
Table 3. Electrical Characteristics	·					
Parameter	Conditio	on	Min	Тур	Max	Unit
Frequency Range			30		3000	MHz
Power Gain @ Psat			10			dB
P <sub>SAT</sub>		15			w	
Drain Efficiency @ P <sub>SAT</sub>		40			%	
Unless otherwise noted: TA = 25°C, $V_{DD}$ =50 \	/, Pulse Width=10	0 us, Duty o	ycle=10%			
Load Mismatch of per Section (On Test Fixtur	e, 50 ohm systen	n): V <sub>DD</sub> =5	) V, I <sub>DQ</sub> =25mA, f =	3GHz		
VSWR 10:1 at P3dB pulse CW Output Power			No Device Degradation			

VSWR 10:1 at P3dB pulse CW Output Power	No Device Degradation
-----------------------------------------	-----------------------

# Innogration (Suzhou) Co., Ltd.

Document Number: SMAV0030-15 Production Datasheet V1.0

**Reference Circuit of Test Fixture Assembly Diagram** 

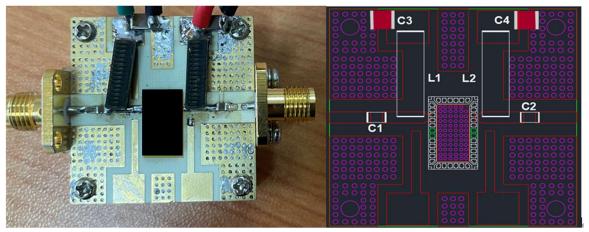
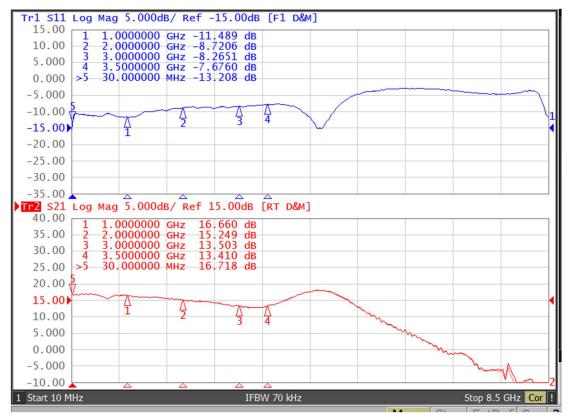


Figure 1. Test Circuit Component Layout

		Part NO.↩
C3, C4🖓	10uF 100V chip Capacitor⇔	43
C1, C2↔	1uF Chip Capacitor₽	43
L1, L2↩	1.3 uH 4.2A Inductor⇔	4310LC-132KEC
PCB⇔⊐	RO4350B, 20mil, Er=3.48↔	¢

### **TYPICAL CHARACTERISTICS**

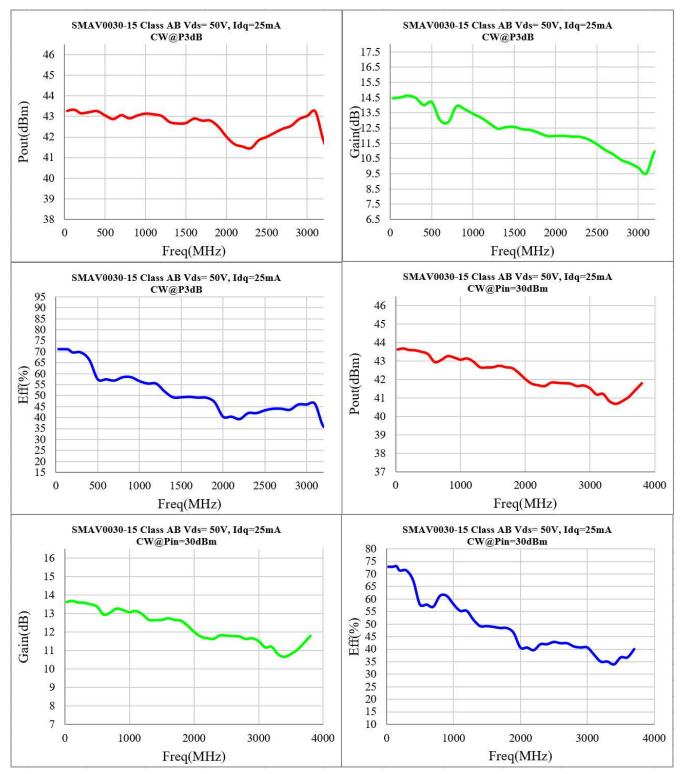
#### Figure 2. Network analyzer output S11/S21 (Pin=0dBm)



# Innogration (Suzhou) Co., Ltd.

#### Document Number: SMAV0030-15 Production Datasheet V1.0

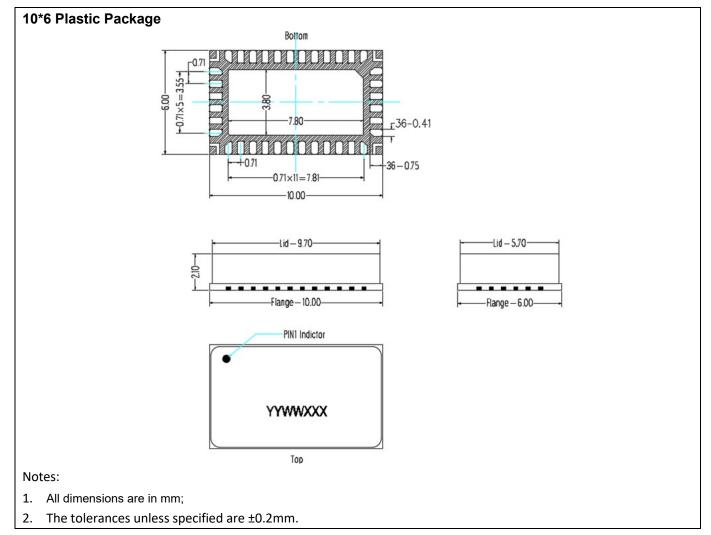
#### Figure 3. Psat, Power Gain and, efficiency vs. Frequency



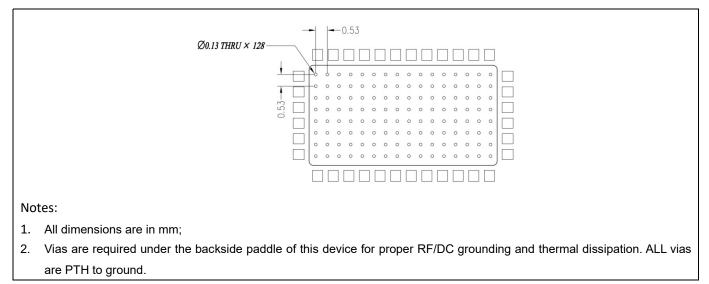


Document Number: SMAV0030-15 Production Datasheet V1.0

### Package Dimensions



### **Mounting Footprint Pattern**



#### **Revision history**

#### Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	V1.0	Production datasheet

Application data based on ZHH-21-18 (2\*1.2)

#### Disclaimers

Specifications are subject to change without notice. Innogration believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogration for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogration . Innogration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogration in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogration and authorized distributors Copyright © by Innogration (Suzhou) Co.,Ltd.